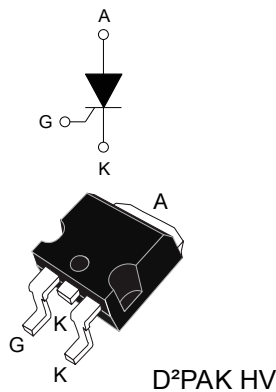



## 40 A 1200 V automotive grade thyristor (SCR)



## Features

- AEC-Q101 qualified 
- High junction temperature: 150 °C
- AC off state voltage: +/- 1200 V
- Nominal on-state RMS current: 40 A<sub>RMS</sub>
- High EFT noise immunity: 1000 V/μs
- Max. gate triggering current: 50 mA
- D²PAK HV creepage distance (anode to cathode):
  - With top coating: 5.38 mm min.
  - Without top coating: 3.48 mm min.
- ECOPACK2 compliant component

## Applications

- On board charger
- Capacitor discharge
- Overvoltage crowbar protection
- Power supplies
- AC switches
- Solid state relays

## Product status

TN4050HP-12G2YTR

## Product summary

$I_{T(RMS)}$	40 A
$V_{DRM}/V_{RRM}$	1200 V
$V_{DSM}/V_{RSM}$	1400 V
$I_{GT}$	50 mA
$T_j$	-40 to 150 °C

## Description

The TN4050HP-12G2YTR is an automotive grade SCR thyristor designed for applications such as automotive on board and stationary battery chargers.

This SCR thyristor, rated for a 40 A RMS power switching, offers superior performances in peak voltage robustness up to 400 V sine wave pulse. Its key features allow the design of functions such as a 56 A RMS AC switch and a 50 V ACDC controlled rectifier-bridge.

The TN4050HP-12G2YTR is available in D²PAK HV surface mount package, ideal for automatic assembly lines.

D²PAK HV package offers increased creepage distance of 5.38 mm, simplifying design conformity with insulation coordination standards such as IEC60664-1 and UL-840.

# 1 Characteristics

**Table 1. Absolute ratings (limiting values)**

Symbol	Parameter		Value	Unit	
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)		40	A	
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)				
$I_{TSM}$	Non repetitive surge peak on-state current, $V_R = 0$ V	$t_p = 8.3$ ms	440	A	
		$t_p = 10$ ms			
$I^2t$	$I^2t$ value for fusing	$t_p = 10$ ms	$T_j = 25$ °C	800	A <sup>2</sup> s
$di/dt$	Critical rate of rise of on-state current, $I_G = 2 \times I_{GT}$ , $t_r \leq 100$ ns	$f = 50$ Hz	$T_j = 150$ °C	200	A/ $\mu$ s
$V_{DRM} / V_{RRM}$	Repetitive off-state voltage		$T_j = 150$ °C	1200	V
$V_{DSM} / V_{RSM}$	Non repetitive surge peak off-state voltage	$t_p = 10$ ms	$T_j = 25$ °C	1400	V
$V_{GM}$	Peak forward gate voltage	$t_p = 20$ $\mu$ s	$T_j = 150$ °C	10	V
$I_{GM}$	Peak forward gate current	$t_p = 20$ $\mu$ s	$T_j = 150$ °C	8	A
$V_{RGM}$	Maximum peak reverse gate voltage		$T_j = 25$ °C	5	V
$P_{G(AV)}$	Average gate power dissipation		$T_j = 150$ °C	1	W
$T_{stg}$	Storage junction temperature range			-40 to +150	°C
$T_j$	Operating junction temperature			-40 to +150	°C

**Table 2. Electrical characteristics ( $T_j = 25$  °C unless otherwise specified)**

Symbol	Test Conditions		Value	Unit	
$I_{GT}$	$V_D = 12$ V, $R_L = 33$ $\Omega$	Min.	10	mA	
		Max.	50		
$V_{GT}$		Max.	1.3	V	
$V_{GD}$	$V_D = 800$ V, $R_L = 3.3$ $\Omega$	$T_j = 150$ °C	Min.	0.2	V
$I_H$	$I_T = 500$ mA, gate open		Max.	100	mA
$I_L$	$I_G = 1.2 \times I_{GT}$		Max.	125	mA
$dV/dt$	$V_D = 800$ V, gate open	$T_j = 150$ °C	Min.	1000	V/ $\mu$ s

**Table 3. Timing Parameters**

Symbol	Test Conditions		Value	Unit	
$t_{gt}$	$I_T = 80$ A, $V_D = 800$ V, $I_G = 100$ mA, $dI_G/dt = 0.2$ A/ $\mu$ s		Typ.	1	$\mu$ s
$t_q$	$I_{TM} = 25$ A, $V_D = 800$ V, $dI_T/dt = 10$ A/ $\mu$ s, $V_R = 75$ V, $dV_D/dt = 20$ V/ $\mu$ s, $t_p = 100$ $\mu$ s	$T_j = 150$ °C	Typ.	150	$\mu$ s

**Table 4. Static Characteristics**

Symbol	Test Conditions			Value	Unit
$V_{TM}$	$I_{TM} = 80\text{ A}$ , $t_p = 380\ \mu\text{s}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	1.55	V
$V_{TO}$	On-state threshold voltage	$T_j = 150\text{ }^\circ\text{C}$	Max.	0.83	V
$R_D$	On-state dynamic resistance	$T_j = 150\text{ }^\circ\text{C}$	Max.	10	m $\Omega$
$I_{DRM}/I_{RRM}$	$V_D = V_{DRM}$ , $V_R = V_{RRM}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	5	$\mu\text{A}$
		$T_j = 125\text{ }^\circ\text{C}$		0.9	mA
		$T_j = 150\text{ }^\circ\text{C}$		6	mA
$I_{DSM}/I_{RSM}$	$V_D = V_{DSM}$ , $V_R = V_{RSM}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	10	$\mu\text{A}$

**Table 5. Thermal parameters**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	Max.	0.4	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient (DC, $S_{CU} = 2.5\text{ cm}^2$ , $e_{CU} = 70\ \mu\text{m}$ )	Typ.	45	

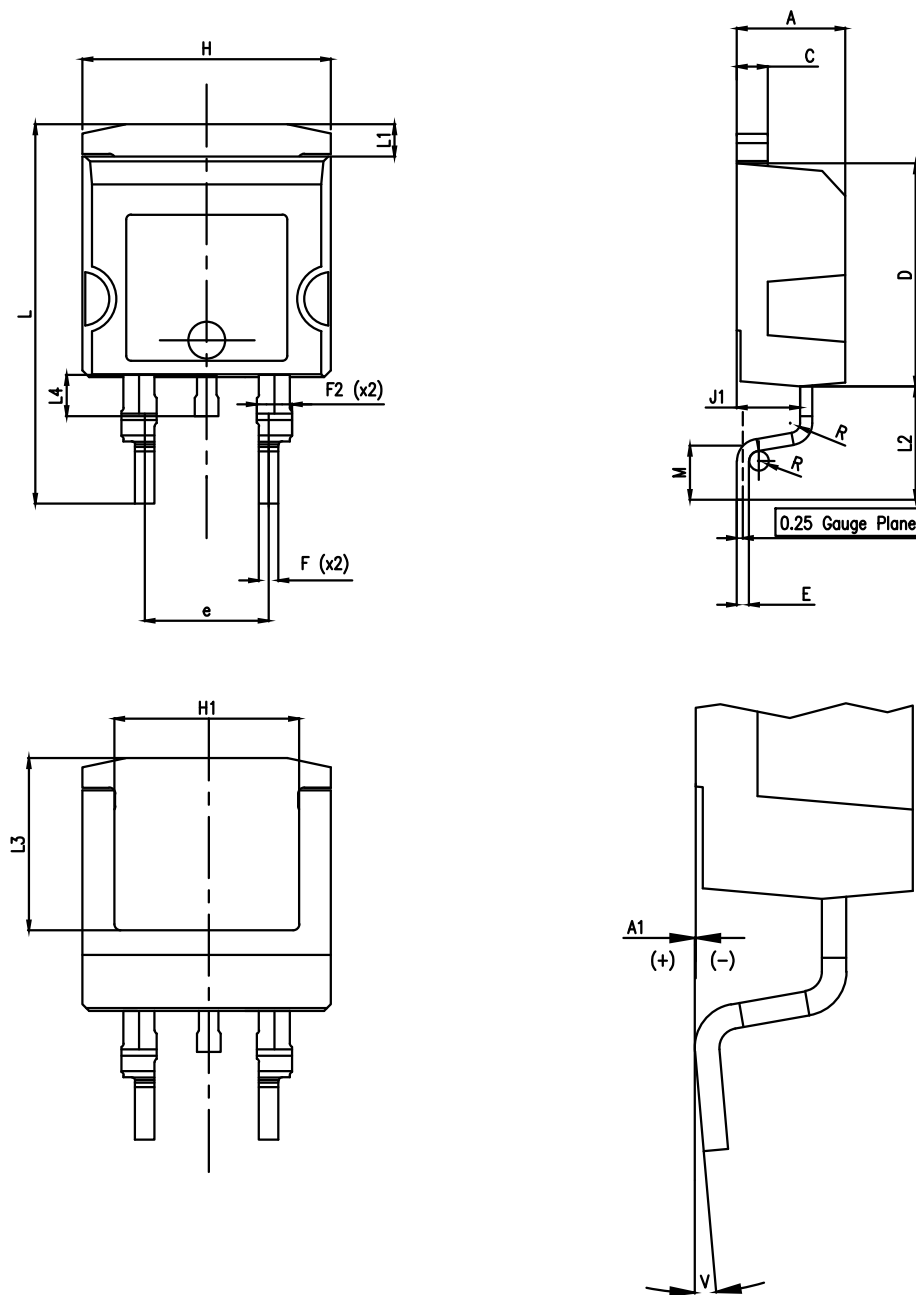
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 2.1 D<sup>2</sup>PAK high voltage package information

- Epoxy meets UL94, V0

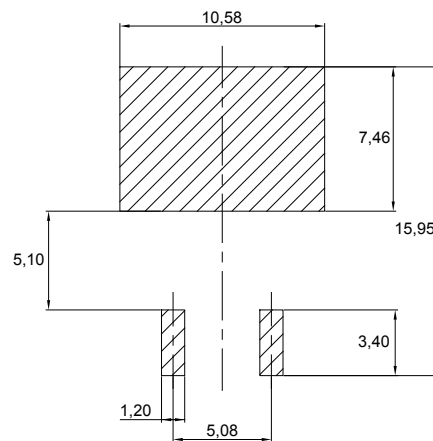
Figure 1. D<sup>2</sup>PAK high voltage package outline



**Table 6. D<sup>2</sup>PAK high voltage package mechanical data**

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.1692	0.1851
A1	0.03	0.20	0.0011	0.0079
C	1.17	1.37	0.0460	0.0540
D	8.95	9.35	0.3523	0.3682
e	4.98	5.18	0.1960	0.2040
E	0.50	0.90	0.0196	0.0355
F	0.78	0.85	0.0307	0.0335
F2	1.14	1.70	0.0448	0.0670
H	10.00	10.40	0.3937	0.4095
H1	7.40	7.80	0.2913	0.3071
J1	2.49	2.69	0.0980	0.1060
L	15.30	15.80	0.6023	0.6221
L1	1.27	1.40	0.0500	0.0552
L2	4.93	5.23	0.1940	0.2060
L3	6.85	7.25	0.2696	0.2855
L4	1.50	1.7	0.0590	0.0670
M	2.60	2.9	0.1023	0.1142
R	0.20	0.60	0.0078	0.0237
V	0°	8°	0°	8°

**Figure 2. D<sup>2</sup>PAK high voltage footprint in mm**



*Note:* For package and tape orientation, reel and inner box dimensions and tape outline please check TN1173.

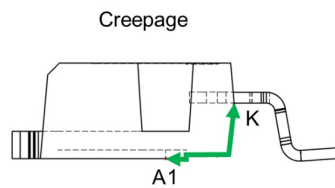
### 2.1.1 Creepage distance between anode and cathode

**Table 7. Creepage distance between anode and cathode**

Symbol	Parameter		Value	Unit
Cd <sub>K-A1</sub>	Minimum creepage distance between K and A1 (with top coating)	D <sup>2</sup> PAK HV	5.38	mm
Cd <sub>K-A2</sub>	Minimum creepage distance between K and A2 (without top coating)		3.48	

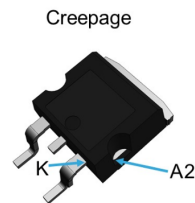
Note: D<sup>2</sup>PAK HV creepage distance (anode to cathode) = 5.38 mm min. (refer to IEC 60664-1)

**Figure 3. Creepage with top coating**



Minimum distance between K & A1 = 5.38 mm (with top coating)

**Figure 4. Creepage without top coating**



Minimum distance between K & A2 = 3.48 mm (without top coating)

### 3 Ordering information

Figure 5. Ordering information scheme

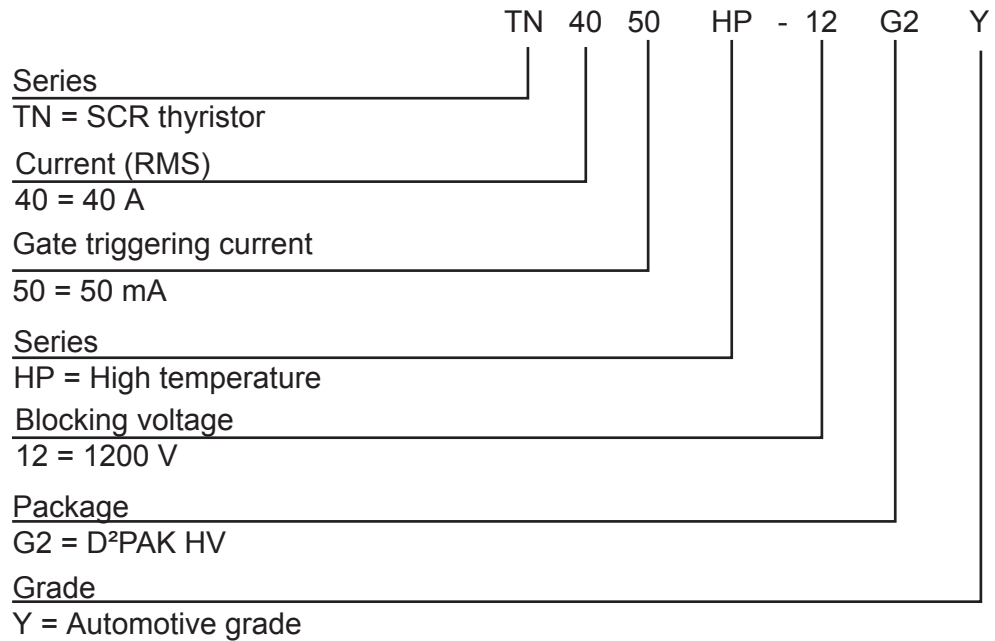


Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN4050HP-12G2YTR	TN40P12YB2	D <sup>2</sup> PAK HV	1.38 g	1000	Tape and reel 13"

## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
20-Jul-2021	1	Initial release.
20-Jul-2021	2	Updated Features and Description on cover page. Updated Table 4. Added Section 2.1.1 Creepage distance between anode and cathode.



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